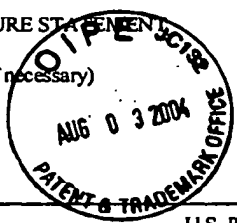
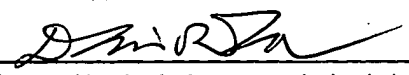


Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 119330		APPLICATION NO. 10/814,169	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Satoshi INOUE FILING DATE April 1, 2004			
							
				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
✓	1	"Single Crystal Thin Film Transistors", IBM Technical Disclosure Bulletin, Aug. 1993, p. 257.					
✓	2	R. Ishihara et al., "Advanced Excimer-Laser Crystallization Techniques of Si Thin-Film For Location Control of Large Grain on Glass", proc. SPIE 2001, Vol. 4295, pp. 14-23.					
EXAMINER					DATE CONSIDERED 1/5/05		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: August 3, 2004